

Package: Exposed Pad SOIC-8

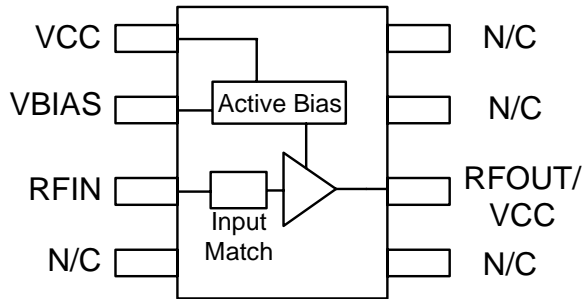


Product Description

RFMD's SPA1118Z is a high efficiency GaAs Heterojunction Bipolar Transistor (HBT) amplifier housed in a low-cost surface-mountable plastic package. These HBT amplifiers are fabricated using molecular beam epitaxial growth technology which produces reliable and consistent performance from wafer to wafer and lot to lot. This product is specifically designed for use as a driver amplifier for infrastructure equipment in the 850MHz band. Its high linearity makes it an ideal choice for wireless data and digital applications.

Optimum Technology Matching® Applied

- GaAs HBT
- GaAs MESFET
- InGaP HBT
- SiGe BiCMOS
- Si BiCMOS
- SiGe HBT
- GaAs pHEMT
- Si CMOS
- Si BJT
- GaN HEMT
- RF MEMS



Features

- High Linearity Performance
- +21dBm IS-95 Channel Power at -55dBc ACP
- +48dBm OIP3 Typ.
- On-Chip Active Bias Control
- Patented High Reliability GaAs HBT Technology
- Surface-Mountable Plastic Package

Applications

- Multi-Carrier Applications
- AMPS, ISM Applications

| Parameter | Specification | | | Unit | Condition |
|------------------------------------|---------------|-------|-------|------|--|
| | Min. | Typ. | Max. | | |
| Frequency of Operation | 810 | | 960 | MHz | |
| Output Power at 1dB Compression | | 29.5 | | dBm | |
| Adjacent Channel Power | | -57.0 | -54.0 | dBc | IS-95 at 880MHz, ±885 KHz, P _{OUT} =21dBm |
| Small Signal Gain | 16.2 | 17.2 | 18.2 | dB | 880MHz |
| Input VSWR | | 1.5:1 | | | |
| Output Third Order Intercept Point | | 48.0 | | dBm | Power out per tone=+14dBm |
| Noise Figure | | 7.5 | | dB | |
| Device Current | 275 | 310 | 330 | mA | |
| Device Voltage | 4.75 | 5.0 | 5.25 | V | |
| Thermal Resistance (junction-lead) | | 35 | | °C/W | T _L =85°C |

Test Conditions: Z₀=50Ω V_{CC}=5V Temp=25°C

Absolute Maximum Ratings

| Parameter | Rating | Unit |
|--|--------|------|
| Max Supply Current (I_{CC}) at V_{CC} typ. | 750 | mA |
| Max Device Voltage (V_{CC}) at I_{CC} typ. | 6.0 | V |
| Max RF Input Power | 24 | dBm |
| Max Junction Temp (T_J) | +160 | °C |
| Max Storage Temp | +150 | °C |
| Moisture Sensitivity Level | 3 | MSL |

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

$$I_D V_D < (T_J - T_L) / R_{TH, J-L}$$



Caution! ESD sensitive device.

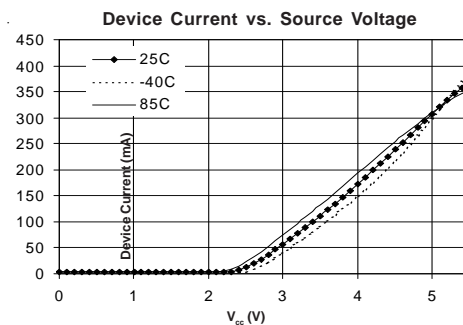
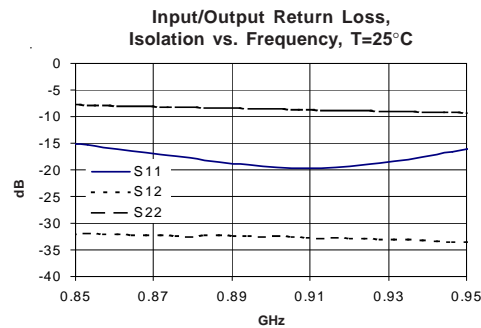
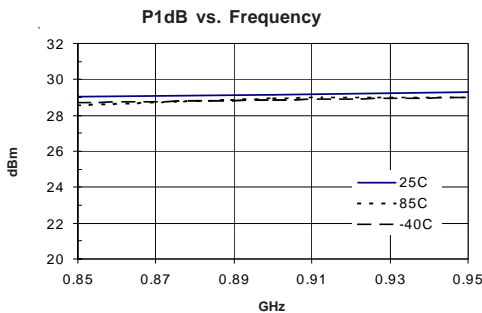
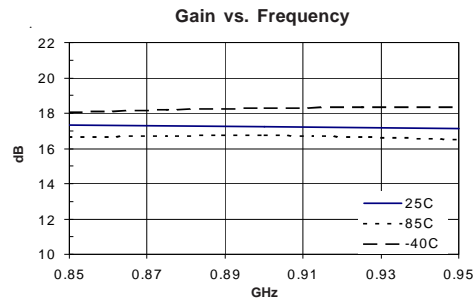
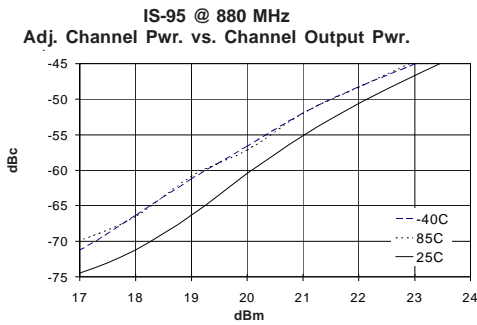
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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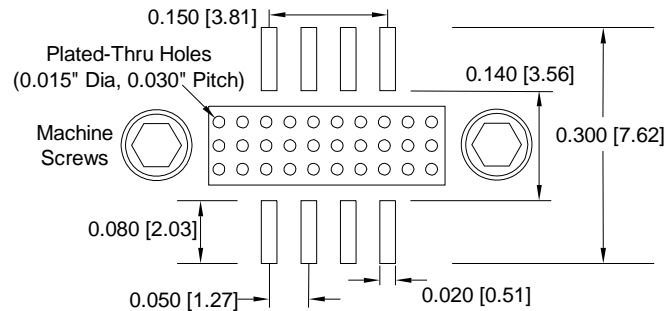
RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

850MHz to 950MHz Application Circuit Data, $I_{CC}=320\text{mA}$, $V_{CC}=5\text{V}$



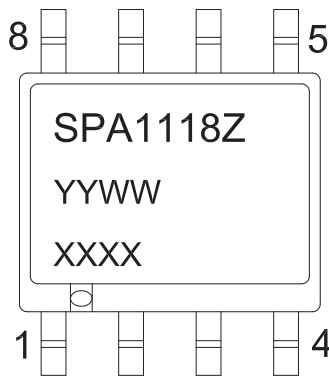
| Pin | Function | Description |
|------|------------|--|
| 1 | VCC | Supply voltage for the active bias network. Bypassing in the appropriate location as shown on the application schematic is required for optimum RF performance. |
| 2 | VBIAS | Bias control pin for the active bias network. Device current is set by the current into this pin. Recommended configuration is shown in the application schematic. Bypassing in the appropriate location as shown on the application schematic is required for optimum RF performance. |
| 3 | RF IN | RF input pin. This pin requires the use of an external DC-blocking capacitor chosen for the frequency of operation. |
| 4, 5 | NC | No connection. |
| 6 | RF OUT/VCC | RF output and bias pin. Bias should be supplied to this pin through an external RF choke. Because DC biasing is present on this pin a DC-blocking capacitor should be used in most applications. The supply side of the bias network should be well bypassed. An output matching network is necessary for optimum performance. |
| 7, 8 | NC | No connection. |
| EPAD | GND | Exposed area on the bottom side of the package needs to be soldered to the ground plane of the board for thermal and RF performance. Several vias should be located under the EPAD as shown in the recommended land pattern. |

Recommended Land Pattern



Note: DIMENSIONS ARE IN INCHES [MM]

Branding Diagram

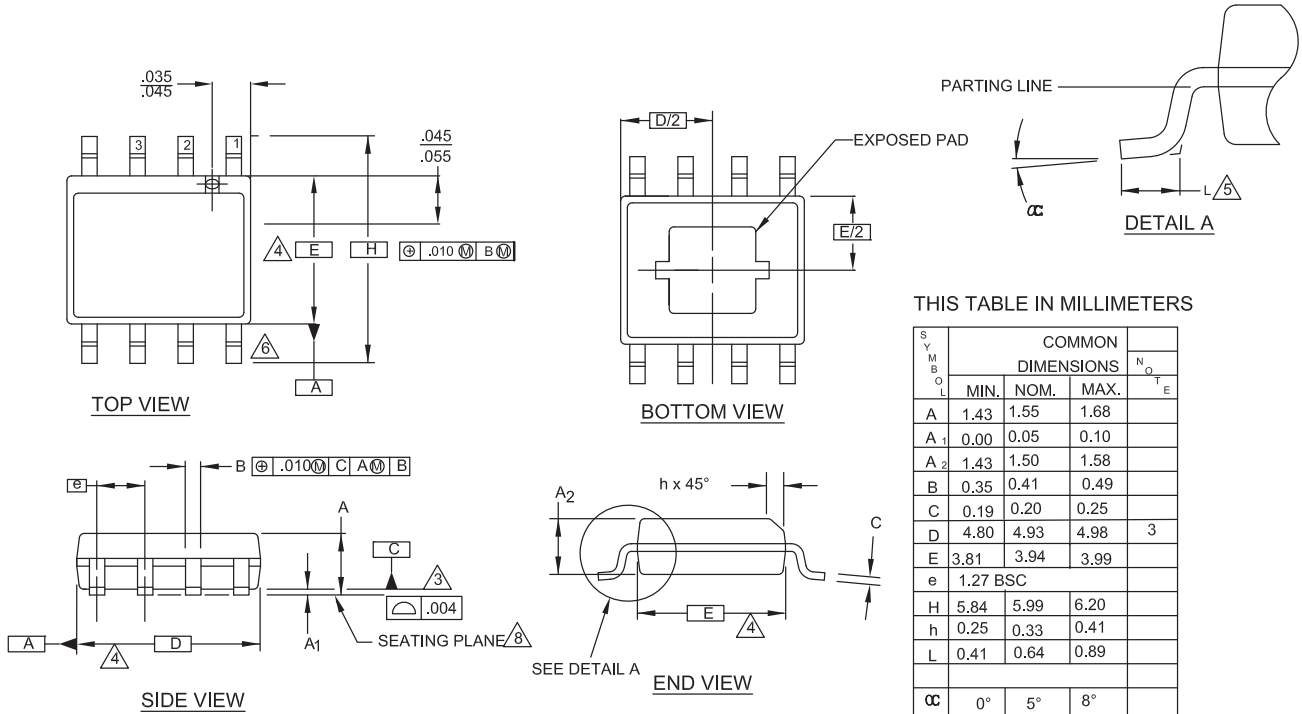


YYWW = DateCode
 XXXX = TraceCode assigned by Subcon

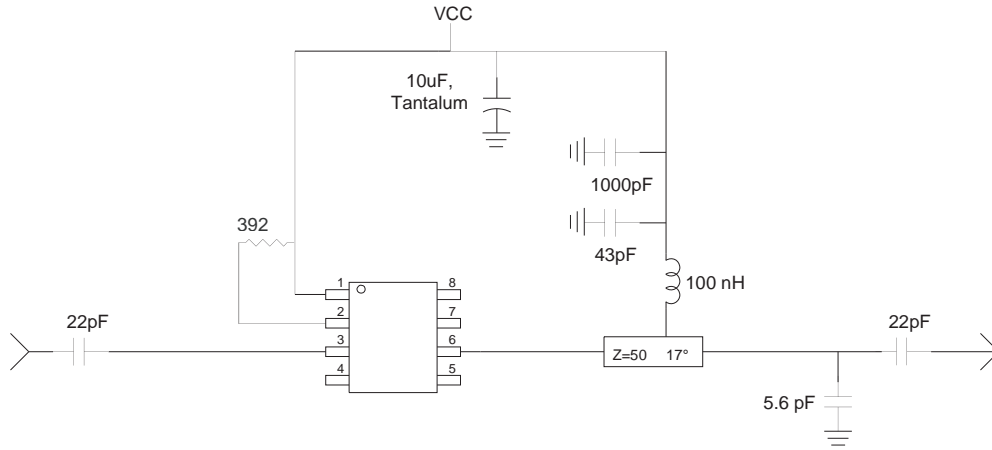
Package Drawing

Dimensions in inches (millimeters)

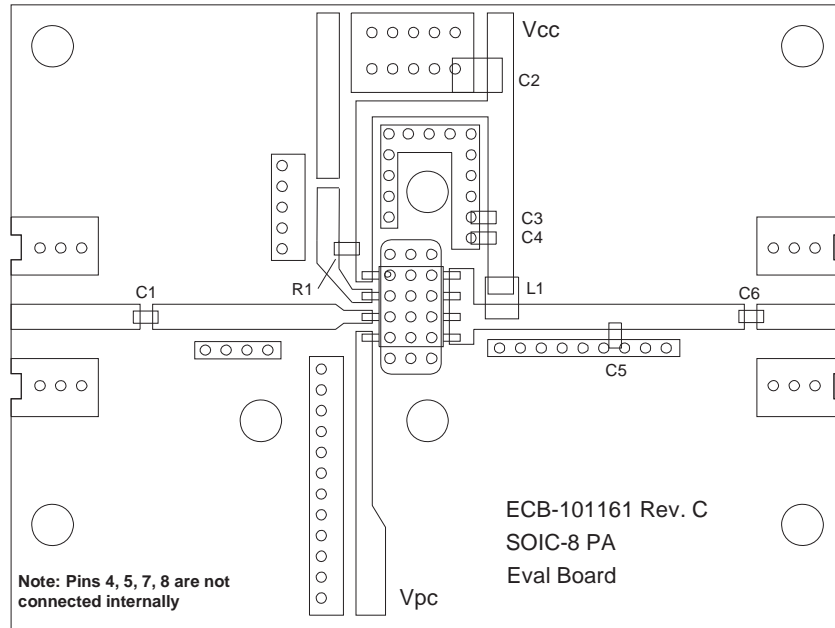
Refer to drawing posted at www.rfmd.com for tolerances.



850 MHz to 950 MHz Application Schematic



Evaluation Board Layout



| Ref. Des. | Value | Part Number |
|-----------|-----------------|-------------------------|
| C1, C6 | 22 pF, 5% | Rohm MCH18 series |
| C2 | 10 uF, 10% | AVX TAJB 106K020R |
| C3 | 1000 pF, 5% | Rohm MCH18 series |
| C4 | 43 pF, 5% | Rohm MCH18 series |
| C5 | 5.6 pF, ±0.5 pF | Rohm MCH18 series |
| L1 | 100 nH, 5% | Coilcraft 1008HQ series |
| R1 | 392Ω, 1% | Rohm MCR03 series |

Ordering Information

| Ordering Code | Description |
|---------------|---|
| SPA1118Z | 7" Reel with 500 pieces |
| SPA1118ZSQ | Sample bag with 25 pieces |
| SPA1118ZSR | 7" Reel with 100 pieces |
| SPA1118Z-EVB1 | 850MHz to 950MHz PCBA with 5-piece sample bag |